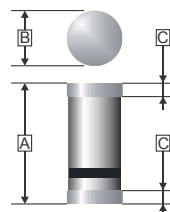


RoHS Compliant Product
A suffix of "-C" specifies halogen & lead-free

FEATURES

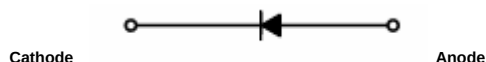
- SOD-80 (Mini-MELF) Package
- Surface Device Type Mounting
- Hermetically Sealed Glass
- Compression Bonded Construction
- All External Surfaces Are Corrosion Resistant And Terminals Are Readily Solderable
- RoHS Compliant
- Matte Tin (Sn) Lead Finish
- Color band Indicates Negative Polarity

SOD-80 (Mini-Melf)



REF.	Millimeter	
	Min.	Max.
A	3.30	3.70
B	1.40	1.60
C	0.28	0.50

ELECTRICAL SYMBOL



MAXIMUM RATINGS AND ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

Parameter	Symbol	Ratings	Unit
Maximum Repetitive Reverse Voltage	V _{RRM}	250	V
Average Rectified Forward Current	I _{F(AV)}	200	mA
Non repetitive Peak Forward Current Pulse Width = 1.0 Second Pulse Width = 1.0 μsecond	I _{FSM}	1.0 4.0	A
Power Dissipation	P _D	500	mW
Thermal Resistance Junction to Ambient	R _{θJA}	350	°C / W
Junction, Storage Temperature	T _J , T _{STG}	200, -65 ~ +200	°C

These ratings are limiting values above which the serviceability of the diode may be impaired.

ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise specified)

Parameters	Symbol	Min.	Max.	Unit	Test Conditions
Breakdown Voltage	BAV100	60	-	V	I _R = 100μA
	BAV101	120	-		
	BAV102	200	-		
	BAV103	250	-		
Reverse Leakage Current	BAV100	-	100	nA	V _R = 50V
	BAV101	-	100		V _R = 100V
	BAV102	-	100		V _R = 150V
	BAV103	-	100		V _R = 200V
Forward Voltage	V _F	-	1.0	V	I _F = 100mA
Capacitance	C	-	5.0	pF	V _R = 0V, f = 1MHz
Reverse Recovery Time	T _{RR}	-	50	nS	I _F = I _R = 30 mA, I _{RR} = 3mA, R _L = 100Ω

CHARACTERISTICS CURVE

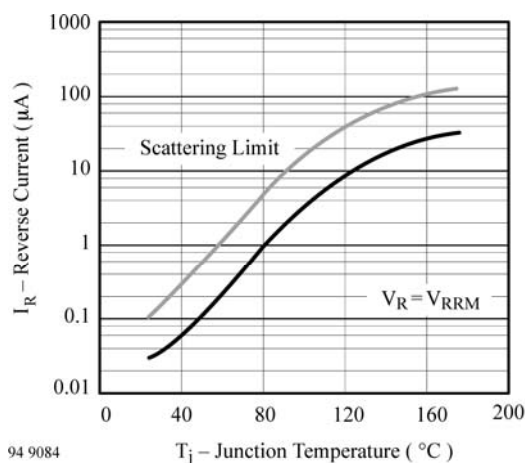


Figure 1. Reverse Current vs. Junction Temperature

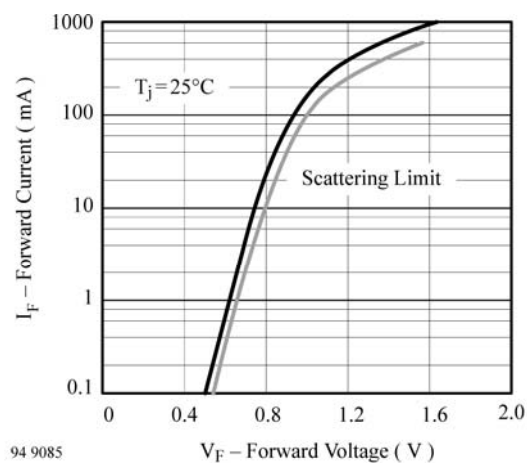


Figure 2. Forward Current vs. Forward Voltage

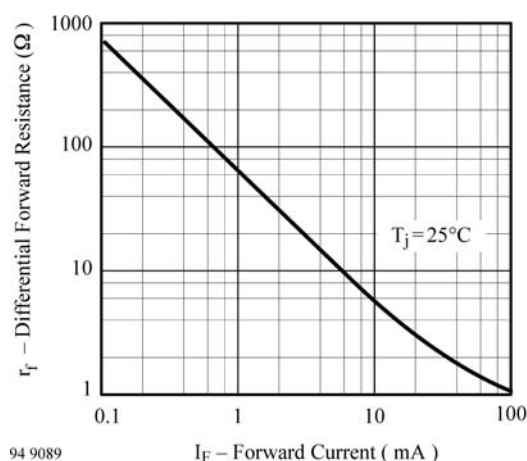


Figure 3. Differential Forward Resistance vs. Forward Current